

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	57mΩ@-10V	-16A
	76mΩ@-4.5V	

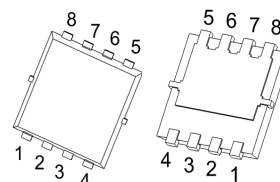
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100% ΔV_{DS} Tested

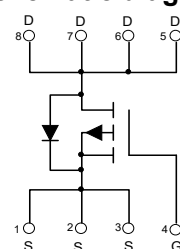
Application

- Power Switching Application

PDFN3.3×3.3-8L



Schematic diagram



MARKING:



M700P06L = Device Code
 XX = Date Code
 Solid Dot = Green Indicator

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V _{DS}	-60	V
Gate - Source Voltage		V _{GS}	±20	V
Continuous Drain Current ¹	T _C = 25℃	I _D	-16	A
	T _C = 100℃	I _D	-10	A
Pulsed Drain Current ²		I _{DM}	-64	A
Single Pulsed Avalanche Current ³		I _{AS}	-17	A
Single Pulsed Avalanche Energy ³		E _{AS}	72	mJ
Power Dissipation ⁵	T _C = 25℃	P _D	30	W
Thermal Resistance from Junction to Ambient ⁶		R _{θJA}	65	℃/W
Thermal Resistance from Junction to Case		R _{θJC}	4.2	℃/W
Junction Temperature		T _J	150	℃
Storage Temperature		T _{STG}	-55~ +150	℃

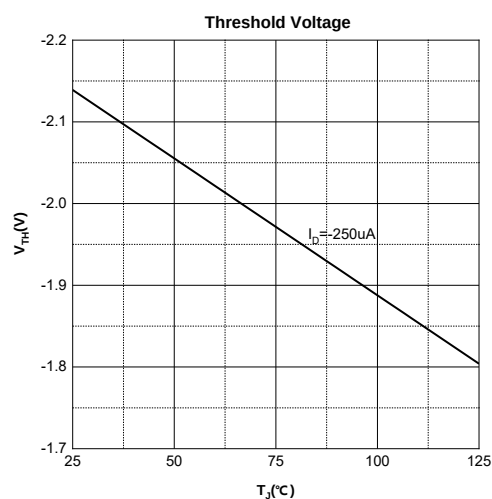
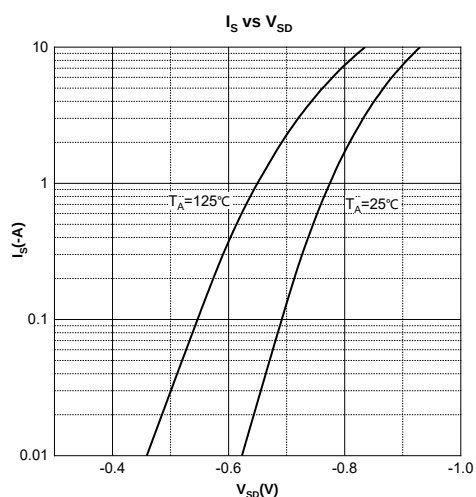
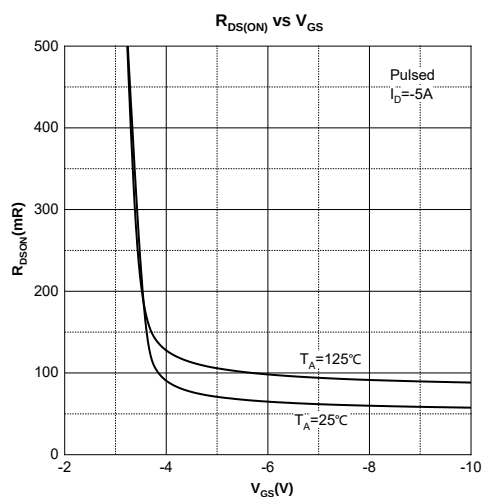
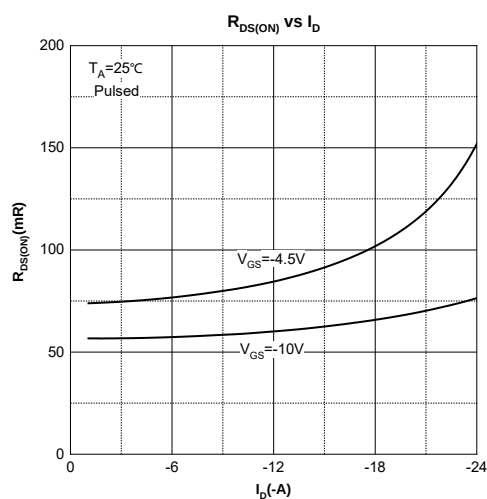
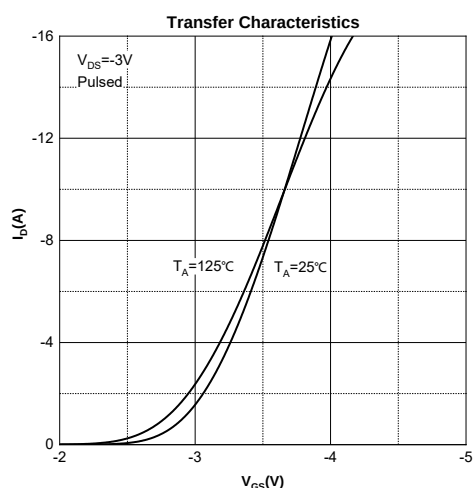
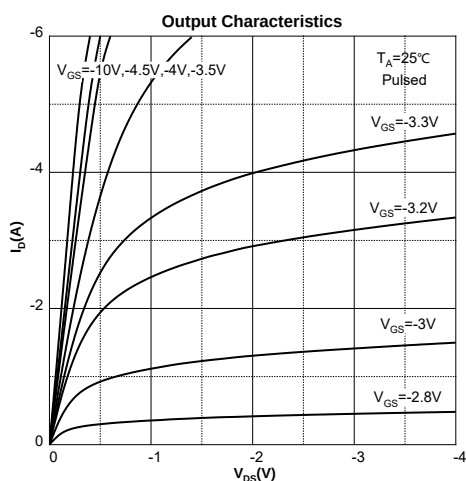
MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

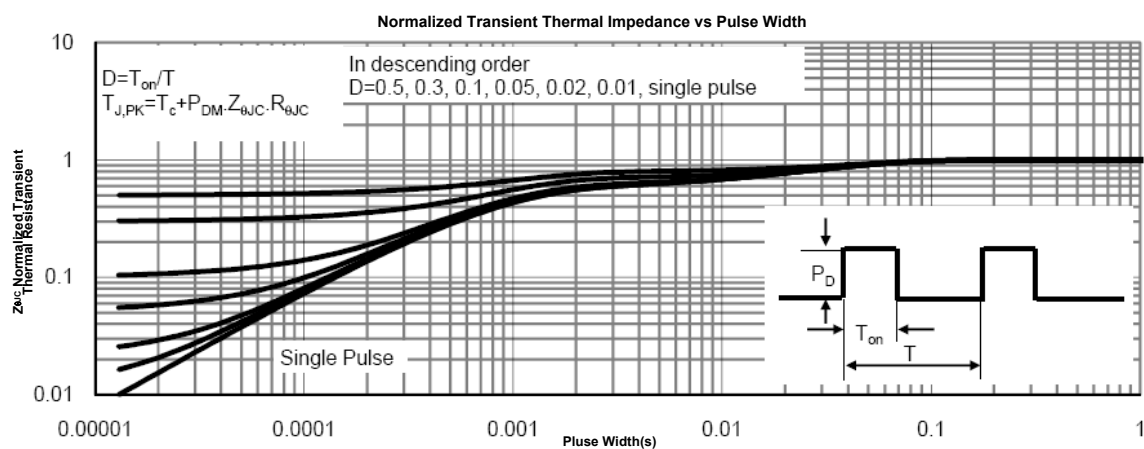
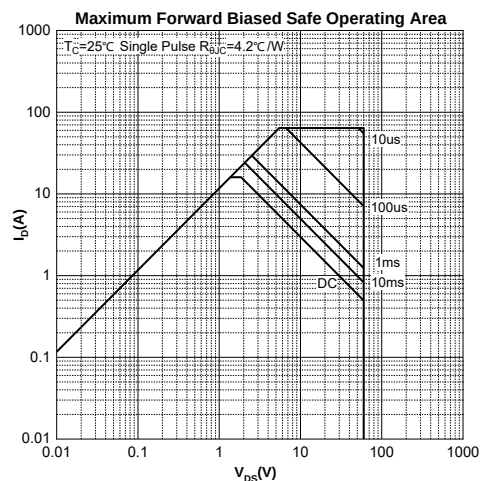
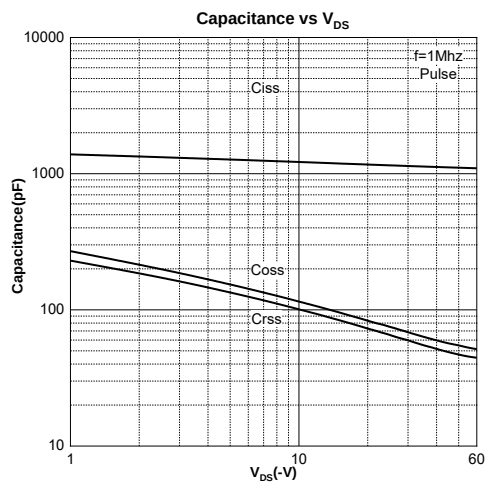
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -48V, V _{GS} = 0V			-1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	-1	-2.2	-3	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -5.7A		57	74	mΩ
		V _{GS} = -4.5V, I _D = -4.4A		76	99	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -30V, V _{GS} = 0V, f = 1MHz		1148		pF
Output Capacitance	C _{oss}			69		
Reverse Transfer Capacitance	C _{rss}			60		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		5.4		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = -30V, V _{GS} = -10V, I _D = -5.7A		23		nC
Gate-source Charge	Q _{gs}			3.8		
Gate-drain Charge	Q _{gd}			6.1		
Turn-on Delay Time	t _{d(on)}	V _{DD} = -30V, V _{GS} = -10V, R _L = 4.3Ω, R _G = 3Ω		9		ns
Turn-on Rise Time	t _r			4		
Turn-off Delay Time	t _{d(off)}			29		
Turn-off Fall Time	t _f			6		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = -10A			-1.2	V

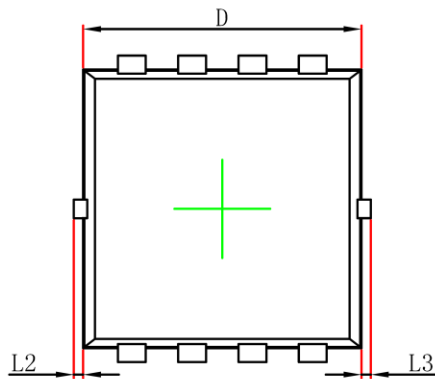
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = -30V, V_{GS} = -10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C.And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

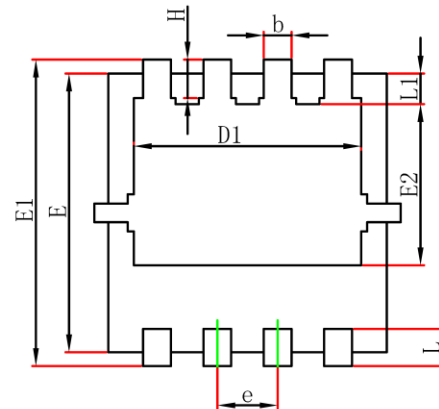
Typical Characteristics



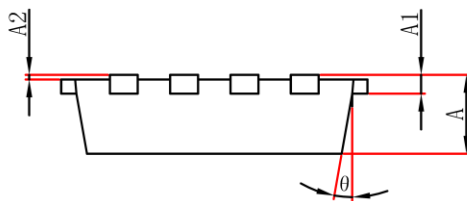


PDFN3.3×3.3-8L Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.152REF		0.006REF	
A2	0.000	0.050	0.000	0.002
D	2.900	3.200	0.114	0.126
D1	2.300	2.600	0.091	0.102
E	2.900	3.200	0.114	0.126
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0.000	0.100	0.000	0.004
L3	0.000	0.100	0.000	0.004
H	0.315	0.515	0.012	0.020
θ	0°	12°	0°	12°